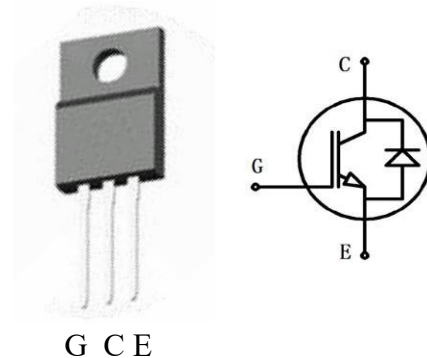


$$V_{CES} = 650V, I_C = 6A, V_{CE(sat)} = 1.7V$$

Features:

- High ruggedness performance
- Very tight parameter distribution
- Positive VCE (sat) temperature coefficient
- High efficiency for motor control
- Excellent current sharing in parallel operation
- RoHS compliant


Applications:

- Home appliances
- Motor drives
- Fan, Pumps, Vacuum cleaner

Absolute Maximum Ratings of IGBT ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Value	Unit
V_{CES}	Collector to Emitter Voltage		650	V
V_{GES}	Continuous Gate to Emitter Voltage		± 20	V
I_C	Continuous Collector Current	$T_C = 100^\circ\text{C}$	6	A
		$T_C = 25^\circ\text{C}$	12	A
I_{CM}	Pulse Collector Current	$t_p = 1\text{ms}$	24	A
P_D	Maximum Power Dissipation (IGBT)	$T_C = 25^\circ\text{C}, T_J = 175^\circ\text{C}$	30	W
t_{sc}	Short Circuit Withstand Time	$V_{CC} = 400V, V_{GE} \leq 15V$	10	μs

Absolute Maximum Ratings of Diode ($T_J = 25^\circ\text{C}$ unless otherwise noted)

V_{RRM}	Repetitive peak reverse voltage	$T_C = 25^\circ\text{C}$	650	V
I_F	Diode Continuous Forward Current	$T_C = 100^\circ\text{C}$	6	A
I_{FM}	Peak FWD Current Repetitive	$t_p = 1\text{ms}$	24	A

Electrical Characteristics of IGBT ($T_J = 25^\circ\text{C}$ unless otherwise noted)
Static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C = 1\text{mA}, V_{CE} = V_{GE}, T_J = 25^\circ\text{C}$	5.2	6.2	7.2	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 6A, V_{GE} = 15V, T_J = 25^\circ\text{C}$	-	1.7	-	V
		$T_J = 175^\circ\text{C}$		2.2		
I_{CES}	Collector-Emitter Leakage Current	$V_{GE} = 0V, V_{CE} = V_{CES}, T_J = 25^\circ\text{C}$	-	-	0.1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE} = \pm 20V, V_{CE} = 0V, T_J = 25^\circ\text{C}$	-100	-	100	nA

C_{iss}	Input capacitance	$V_{CE}=30V,$ $V_{GE}=0V,$ $f=1MHz$	-	480	-	pF
C_{oss}	Output capacitance		-	22	-	
C_{rss}	Reverse transfer capacitance		-	8	-	
Q_g	Total gate charge	$V_{CC}=520V$ $V_{GE}=15V$ $I_C=6A$	-	19	-	nC

Switching Characteristics

t _{d(on)}	Turn-on Delay Time	V _{CC} =400V, I _C =6A, V _{GE} =±15V, L=525uH, R _G =10Ω	T _J = 25°C		10		ns
			T _J = 175°C		11		
t _r	Rise Time		T _J = 25°C		8		ns
			T _J = 175°C		10		
t _{d(off)}	Turn-off Delay Time		T _J = 25°C		79		ns
			T _J = 175°C		108		
t _f	Fall Time		T _J = 25°C		56		ns
			T _J = 175°C		89		
E _{on}	Turn-on Switching Loss		T _J = 25°C		0.11		mJ
			T _J = 175°C		0.16		
E _{off}	Turn-off Switching Loss		T _J = 25°C		0.1		mJ
			T _J = 175°C		0.16		
R _{θJC}	Junction-To-Case (IGBT)					5.0	K/W

Electrical Characteristics of Diode ($T_J = 25^\circ C$ unless otherwise noted)
Static characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{FM}	Forward Voltage	$I_F=6A, V_{GE}=0V$	$T_J = 25^\circ C$		1.6		V
			$T_J = 150^\circ C$		1.4		

Switching Characteristics

IRM	Peak Reverse Recovery Current	I _F =6A, V _{CC} =400V, V _{GE} =-15V, L=525uH, R _G =10Ω	T _J = 25°C		10		A
			T _J = 175°C		12		
Q _{rr}	Reverse Recovery Charge		T _J = 25°C		306		nC
			T _J = 175°C		529		
t _{rr}	Reverse Recovery Energy		T _J = 25°C		55		ns
			T _J = 175°C		98		
R _{θJC}	Junction-To-Case (Diode)					5.8	K/W

Module Characteristics

T_J	Maximum Junction Temperature			175	$^\circ C$
T_{JOP}	Maximum Operating Junction Temperature Range	-40		+175	$^\circ C$
T_{stg}	Storage Temperature	-55		+150	$^\circ C$

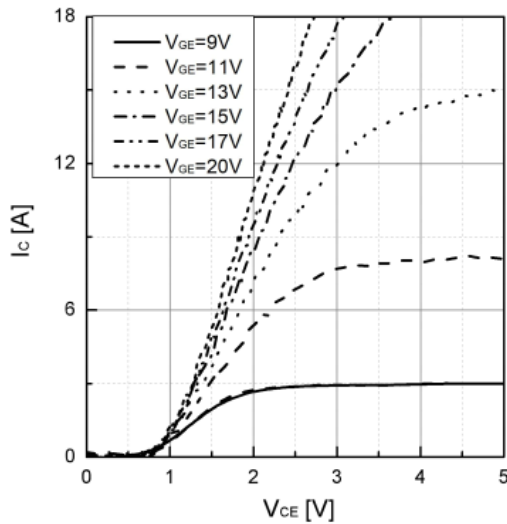


Fig 1. Typical output characteristic ($T_{vj}=25^{\circ}\text{C}$)

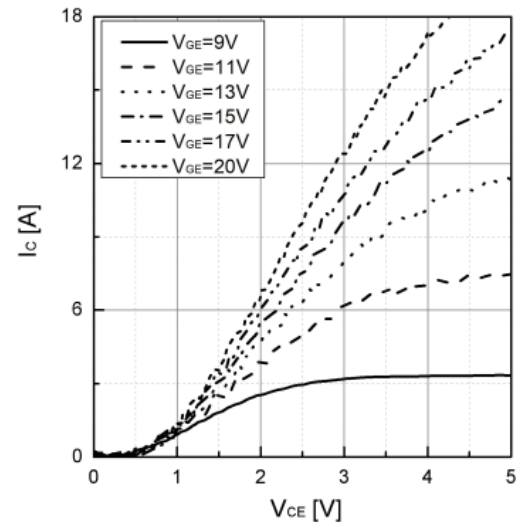


Fig 2. Typical output characteristic ($T_{vj}=175^{\circ}\text{C}$)

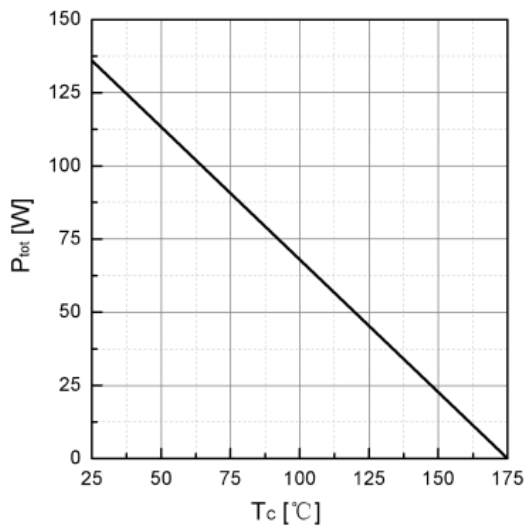


Fig 3. Power dissipation as a function of T_c

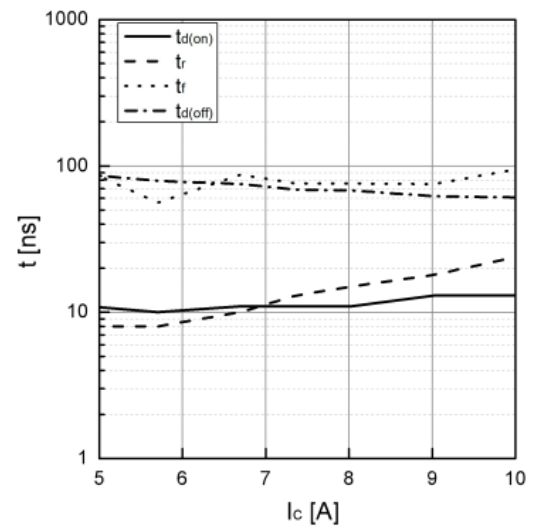


Fig 4. Typical switching time as a function of I_c

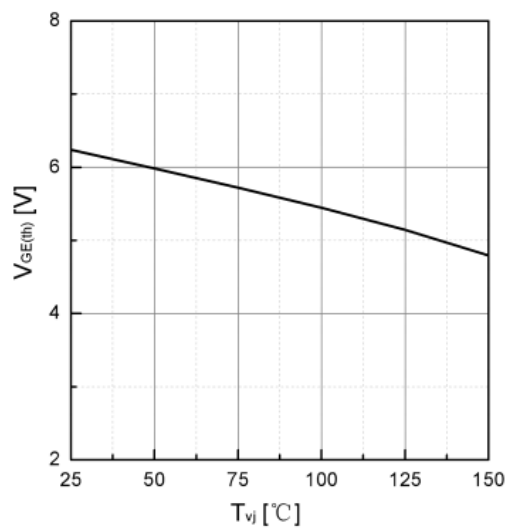


Fig 5. Typical $V_{GE(th)}$ as a function of T_{vj}
($I_c=1\text{mA}$)

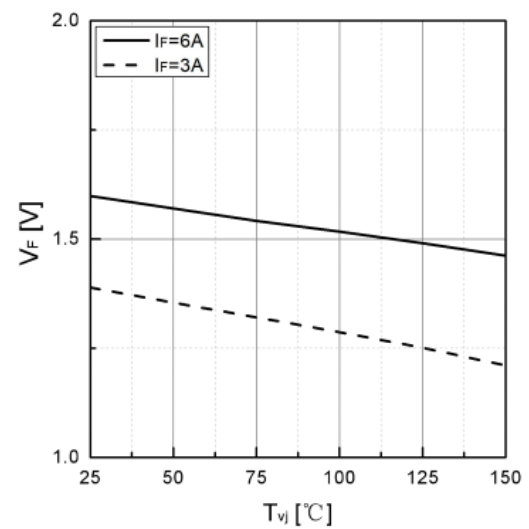


Fig 6. Typical V_F as a function of T_{vj}

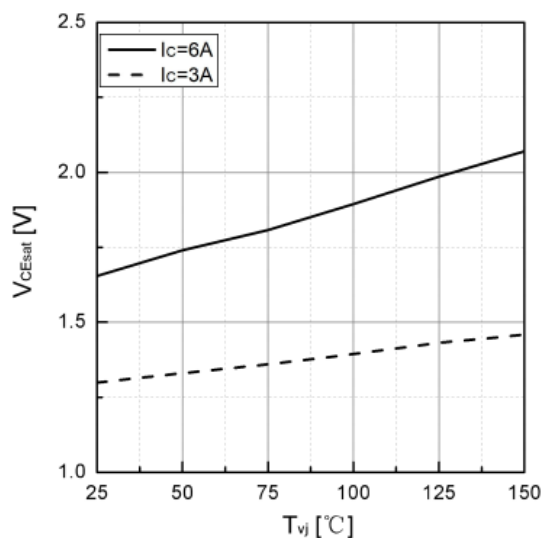


Fig 7. Typical V_{CEsat} as a function of T_{vj}

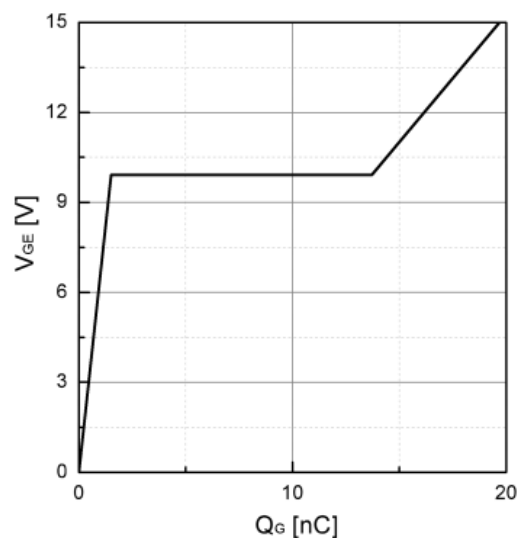


Fig 8. Typical Gate charge

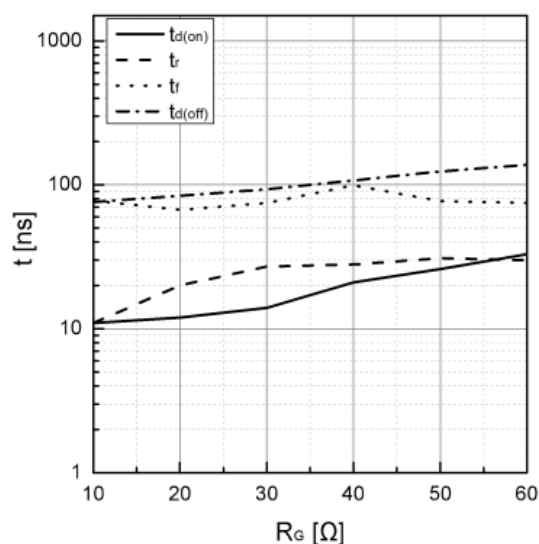


Fig 9. Typical switching times as a function of R_G

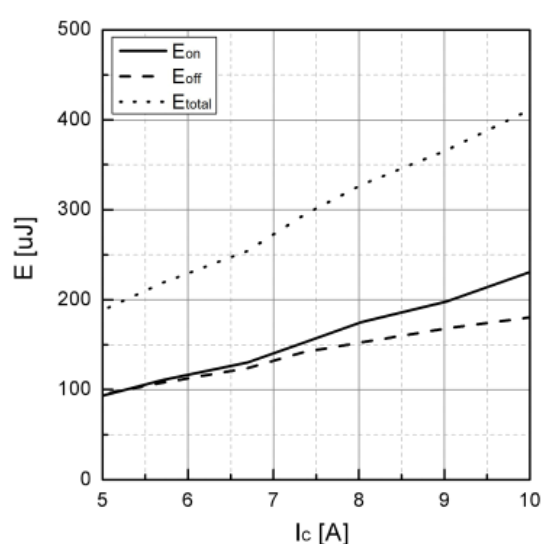


Fig 10. Typical switching energy losses as a function of I_c

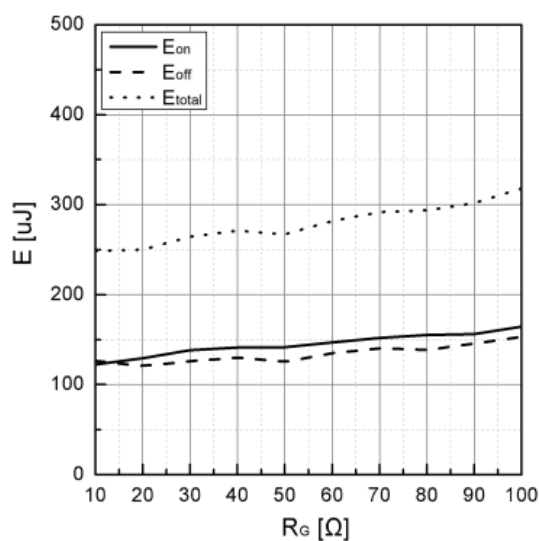


Fig 11. Typical switching energy losses as a function of R_G

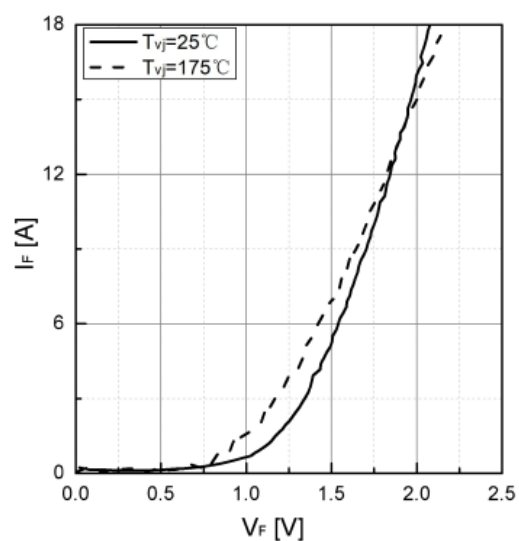


Fig 12. Typical I_F as a function of V_F

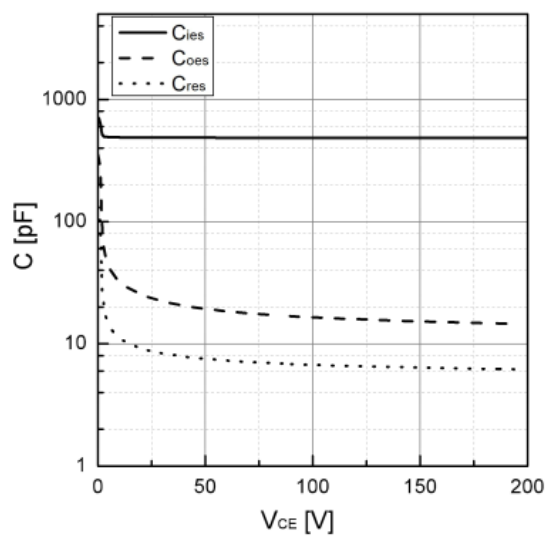
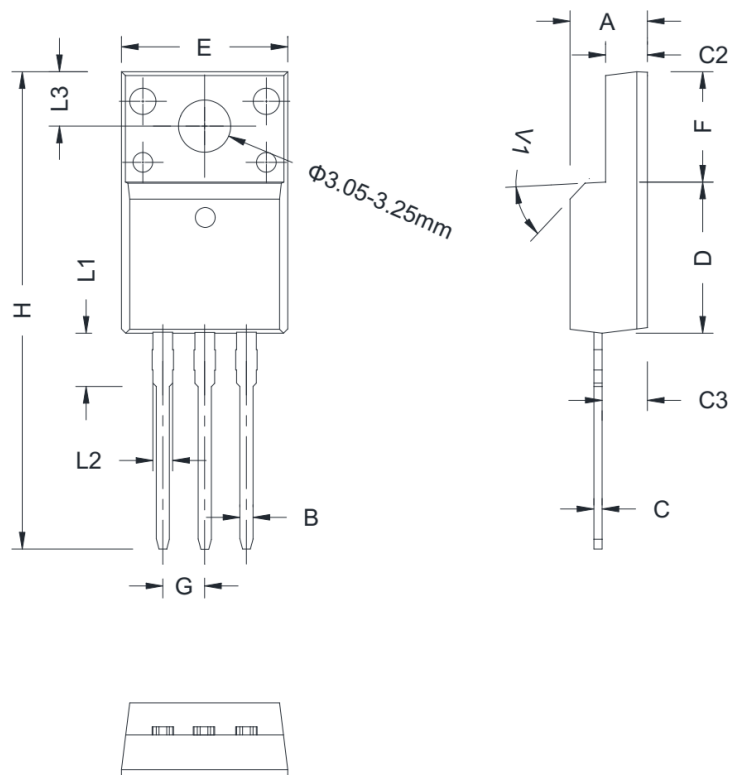


Fig 13. Typical capacitance as a function of V_{CE}
 (f=1Mhz, $V_{GE}=0V$)

Package Outline :

TO-220F



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50	-	4.90	0.177	-	0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47	-	0.66	0.019	-	0.026
C2	2.45	-	2.75	0.096	-	0.108
C3	2.60	-	3.00	0.102	-	0.118
D	8.80	-	9.30	0.346	-	0.366
E	9.80	-	10.40	0.386	-	0.410
F	6.40	-	6.80	0.252	-	0.268
G	2.40	-	2.70	0.094	-	0.106
H	28.0	-	29.80	1.102	-	1.173
L1	-	3.63	-	-	0.143	-
L2	1.14	-	1.70	0.045	-	0.067
L3	-	3.30	-	-	0.130	-
V1	-	45°	-	-	45°	-

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